

## **General Description**

The WST6004 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The WST6004 meet the RoHS and Green Product requirement with full function reliability approved.

### **Features**

- High-speed switching
- Green Device Available

### **Product Summery**

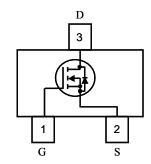
BVDSS	RDSON	ID
20V	140mΩ	0.6A

### **Applications**

- Replace Digital Transistor
- Power Supply Converter Circuits
- ●Load/Power Switching Cell Phones, Pagers

# **SOT-523 Pin Configuration**





## **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	20	V
$V_{GS}$	Gate-Source Voltage	±8	V
I <sub>D</sub> @T <sub>A</sub> =25℃	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	600	mA
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	300	mA
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	3	Α
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>3</sup>	0.175	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	$^{\circ}$
TJ	Operating Junction Temperature Range	-55 to 150	$^{\circ}$ C

### **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit
R <sub>0JA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>		625	°C/W

**N-Ch MOSFET** 

# Electrical Characteristics (T<sub>J</sub>=25 C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	20			V	
$\triangle BV_{DSS}/\triangle T_{J}$	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25℃, I <sub>D</sub> =1mA		0.05		V/°C	
Б	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V , I <sub>D</sub> =0.6A		140	450	mΩ	
R <sub>DS(ON)</sub>	Static Diain-Source On-Resistance	V <sub>GS</sub> =2.5V , I <sub>D</sub> =0.5A		180	765		
V <sub>GS(th)</sub>	Gate Threshold Voltage	V -V I -250A	0.35		1.0	V	
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	$V_{GS}=V_{DS}$ , $I_D=250uA$		-3.7		mV/℃	
l	Drain-Source Leakage Current	$V_{DS}$ =16V , $V_{GS}$ =0V , $T_{J}$ =25 $^{\circ}$ C			1	- uA	
I <sub>DSS</sub>		$V_{DS}$ =16V , $V_{GS}$ =0V , $T_J$ =55 $^{\circ}$ C			5		
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}$ = $\pm 8V$ , $V_{DS}$ = $0V$			±10	uA	
gfs	Forward Transconductance	$V_{DS}$ =5V , $I_D$ =0.1A		880		mS	
T <sub>d(on)</sub>	Turn-On Delay Time			6			
Tr	Rise Time	$V_{DD}$ =15V , $V_{GS}$ =10V ,		3.8		no	
$T_{d(off)}$	Turn-Off Delay Time	$R_G=3.3\Omega$ , $I_D=0.1A$		28		ns	
T <sub>f</sub>	Fall Time			18			
C <sub>iss</sub>	Input Capacitance			130	220		
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz		20	36	pF	
C <sub>rss</sub>	Reverse Transfer Capacitance			16	28		

### **Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current <sup>1,4</sup>	V =V =0V Force Current			100	mA
I <sub>SM</sub>	Pulsed Source Current <sup>2,4</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			0.5	Α
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}$ =0V , $I_S$ =0.2A , $T_J$ =25 $^{\circ}$ C			1	V

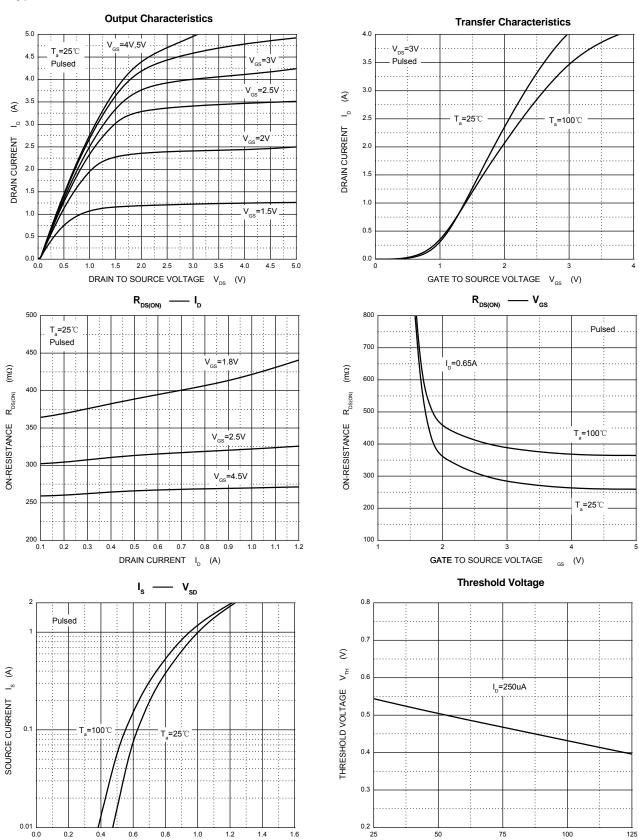
#### Note:

- 1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\,\leq\,$  300us , duty cycle  $\,\leq\,$  2%
- 3.The power dissipation is limited by 150 ℃ junction temperature.
- 4. The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.



**N-Ch MOSFET** 

### **Typical Performance Characteristics**



JUNCTION TEMPERATURE  $T_i$  (°C)

8.0

SOURCE TO DRAIN VOLTAGE

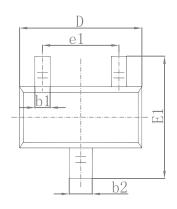
1.0

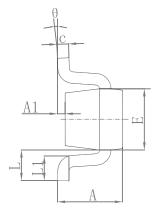
<sub>SD</sub> (V)

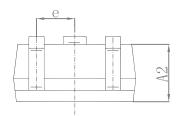
1.4



# **SOT-523 Package Outline Dimensions**

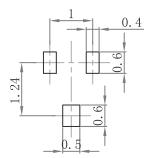






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	0.700	0.900	0.028	0.035	
A1	0.000	0.100	0.000	0.004	
A2	0.700	0.800	0.028	0.031	
b1	0.150	0.250	0.006	0.010	
b2	0.250	0.350	0.010	0.014	
С	0.100	0.200	0.004	0.008	
D	1.500	1.700	0.059	0.067	
E	0.700	0.900	0.028	0.035	
E1	1.450	1.750	0.057	0.069	
е	0.500	TYP.	0.020 TYP.		
e1	0.900	1.100	0.035	0.043	
L	0.400 REF.		0.016	REF.	
L1	0.260	0.460	0.010	0.018	
K	0°	8°	0°	8°	

# **SOT-523 Suggested Pad Layout**





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